

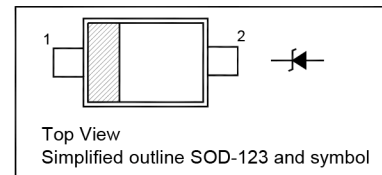
Silicon Planar Zener Diodes

Features

- Total power dissipation: Max. 500 mW
- Small plastic package suitable for surface mounted design
- Tolerance approximately $\pm 5\%$

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	$R_{\theta\text{JA}}$	350	$^\circ\text{C/W}$
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.9	V

Characteristics at $T_a = 25^\circ\text{C}$

Type	Marking Code	Zener Voltage ¹⁾				Maximum Dynamic Impedance				Leakage Current	
		V_{ZT}			at I_{ZT}	Z_{ZT}	at I_{ZT}	Z_{ZK}	at I_{ZK}	I_R	at V_R
		Nom. (V)	Min. (V)	Max. (V)	(mA)	Max.(Ω)	(mA)	Max.(Ω)	(mA)	Max.(μA)	(V)
MM1Z5244B	ZR	14	13.3	14.7	9	15	9	600	0.25	0.1	10

¹⁾ V_{ZT} is tested with pulses (20 ms)